

1. Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology.

1.2 Features and benefits

- Lead-free package
- Logic level compatible
- Optimized for use in DC-to-DC converters
- Very low switching and conduction losses

1.3 Applications

- DC-to-DC convertors
- Notebook computers
- Switched-mode power supplies
- Voltage regulators

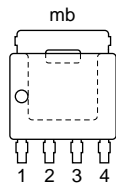
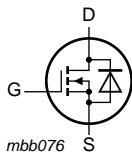
1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 150\text{ °C}$	-	-	30	V
I_D	drain current	$T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1 ; see Figure 3	-	-	76.7	A
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 4.5\text{ V}$; $I_D = 25\text{ A}$; $V_{DS} = 12\text{ V}$; see Figure 11 ; see Figure 12	-	3.1	-	nC
Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; see Figure 9 ; see Figure 10	-	4.7	6	m Ω

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1, 2, 3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

**SOT669
(LFAK)**

3. Ordering information

Table 3. Ordering information

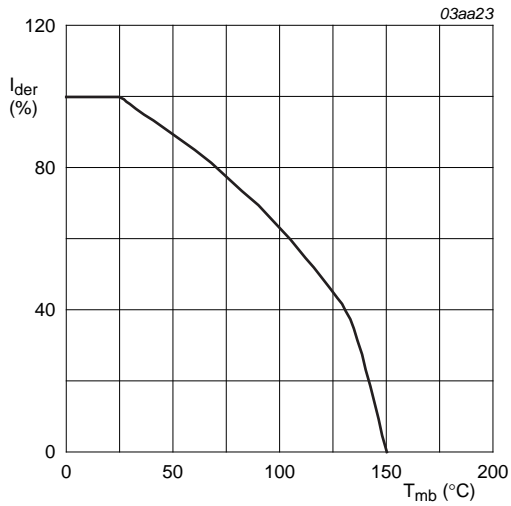
Type number	Package		Description	Version
	Name			
PH6030L	LFAK		Plastic single-ended surface-mounted package (LFAK); 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

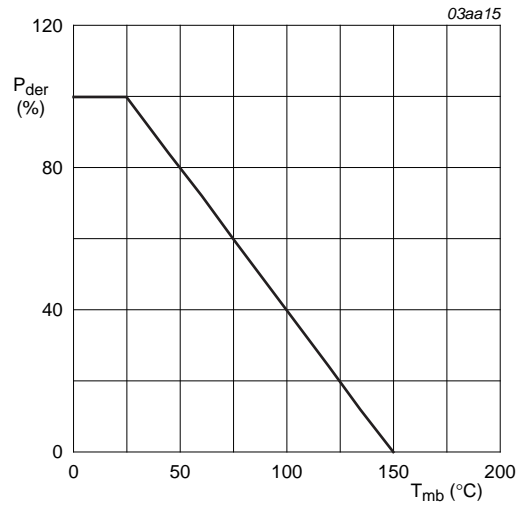
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 150\text{ °C}$	-	30	V
V_{DGR}	drain-gate voltage	$25\text{ °C} \leq T_j \leq 150\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 100\text{ °C}$; see Figure 1	-	48.5	A
		$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; see Figure 1 ; see Figure 3	-	76.7	A
I_{DM}	peak drain current	$t_p \leq 10\text{ }\mu\text{s}$; pulsed; $T_{mb} = 25\text{ °C}$; see Figure 3	-	300	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	62.5	W
T_{stg}	storage temperature		-55	150	°C
T_j	junction temperature		-55	150	°C
Source-drain diode					
I_S	source current	$T_{mb} = 25\text{ °C}$	-	52	A
I_{SM}	peak source current	$t_p \leq 10\text{ }\mu\text{s}$; pulsed; $T_{mb} = 25\text{ °C}$	-	208	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; $I_D = 31\text{ A}$; $V_{sup} \leq 30\text{ V}$; $t_p = 0.14\text{ ms}$; $R_{GS} = 50\text{ }\Omega$; unclamped inductive load	-	95	mJ



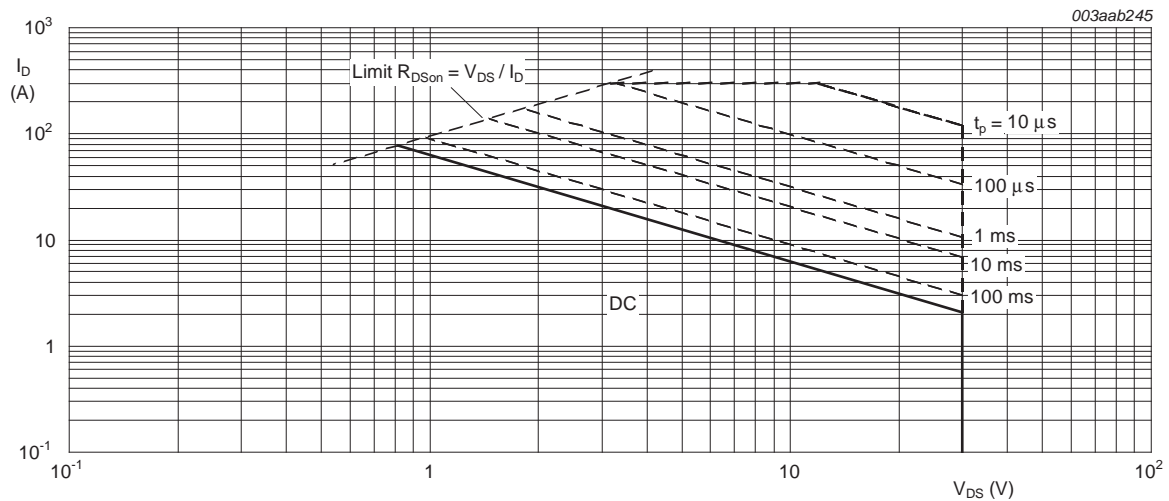
$$I_{der} = \frac{I_D}{I_{D(25^\circ\text{C})}} \times 100\%$$

Fig 1. Normalized continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25^\circ\text{C}; I_{DM}$ is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	2	K/W

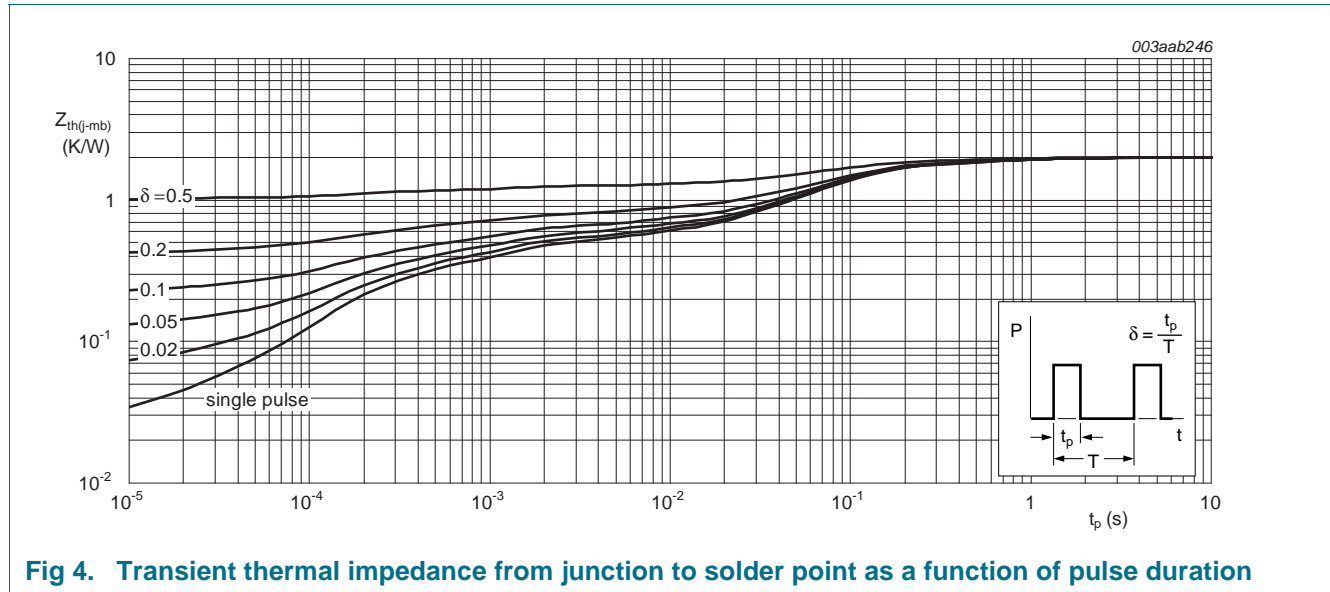


Fig 4. Transient thermal impedance from junction to solder point as a function of pulse duration

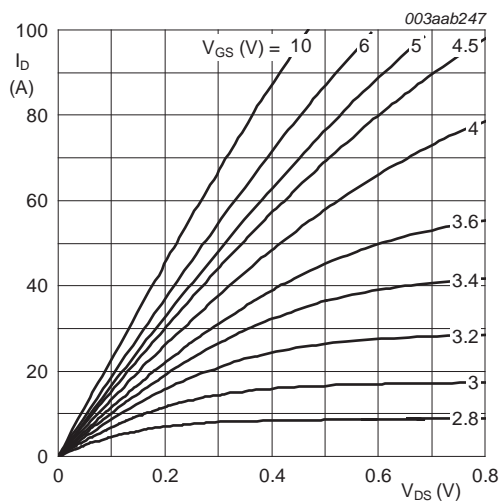
6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A$; $V_{GS} = 0 V$; $T_j = -55 \text{ }^\circ C$	27	-	-	V
		$I_D = 250 \mu A$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$	30	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ }^\circ C$; see Figure 7	-	-	2.6	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 150 \text{ }^\circ C$; see Figure 7	0.8	-	-	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ }^\circ C$; see Figure 7 ; see Figure 8	1.3	1.7	2.15	V
I_{DSS}	drain leakage current	$V_{DS} = 30 V$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	-	1	μA
		$V_{DS} = 30 V$; $V_{GS} = 0 V$; $T_j = 150 \text{ }^\circ C$	-	-	100	μA
I_{GSS}	gate leakage current	$V_{GS} = 16 V$; $V_{DS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = -16 V$; $V_{DS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	-	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 V$; $I_D = 25 A$; $T_j = 150 \text{ }^\circ C$; see Figure 9	-	8.5	10.6	m Ω
		$V_{GS} = 4.5 V$; $I_D = 25 A$; $T_j = 25 \text{ }^\circ C$; see Figure 9 ; see Figure 10	-	7.3	9.7	m Ω
		$V_{GS} = 10 V$; $I_D = 25 A$; $T_j = 25 \text{ }^\circ C$; see Figure 9 ; see Figure 10	-	4.7	6	m Ω
R_G	gate resistance	$f = 1 \text{ MHz}$	-	1.75	-	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 25 A$; $V_{DS} = 12 V$; $V_{GS} = 4.5 V$; see Figure 11 ; see Figure 12	-	15.2	-	nC
		$I_D = 0 A$; $V_{DS} = 0 V$; $V_{GS} = 4.5 V$; see Figure 11	-	14	-	nC
Q_{GS}	gate-source charge	$I_D = 25 A$; $V_{DS} = 12 V$; $V_{GS} = 4.5 V$; see Figure 12 ; see Figure 12	-	8.5	-	nC
Q_{GD}	gate-drain charge		-	3.1	-	nC
Q_{GS1}	pre-threshold gate-source charge		-	4.1	-	nC
Q_{GS2}	post-threshold gate-source charge		-	4.4	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25 A$; $V_{DS} = 12 V$; see Figure 11 ; see Figure 12	-	3.5	-	V
C_{iss}	input capacitance	$V_{DS} = 12 V$; $V_{GS} = 0 V$; $f = 1 \text{ MHz}$; $T_j = 25 \text{ }^\circ C$; see Figure 13	-	2260	-	pF
		$V_{DS} = 0 V$; $V_{GS} = 0 V$; $f = 1 \text{ MHz}$; $T_j = 25 \text{ }^\circ C$; see Figure 13	-	2540	-	pF
C_{oss}	output capacitance	$V_{DS} = 12 V$; $V_{GS} = 0 V$; $f = 1 \text{ MHz}$; $T_j = 25 \text{ }^\circ C$; see Figure 13	-	460	-	pF
C_{rss}	reverse transfer capacitance		-	210	-	pF

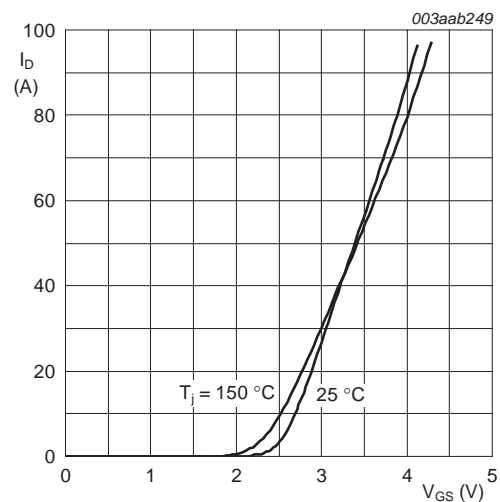
Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{d(on)}$	turn-on delay time	$V_{DS} = 12\text{ V}; R_L = 0.5\ \Omega; V_{GS} = 4.5\text{ V};$	-	25	-	ns
t_r	rise time	$R_{G(ext)} = 5.6\ \Omega$	-	53	-	ns
$t_{d(off)}$	turn-off delay time		-	27	-	ns
t_f	fall time		-	14	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ see Figure 14	-	0.85	1.2	V
t_{rr}	reverse recovery time	$I_S = 20\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V}; V_{DS} = 30\text{ V}$	-	34	-	ns
Q_r	recovered charge	$I_S = 20\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V}$	-	11.5	-	nC



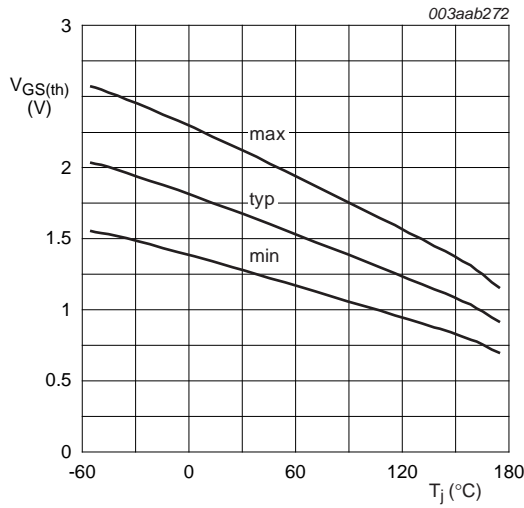
$T_j = 25\text{ }^\circ\text{C}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



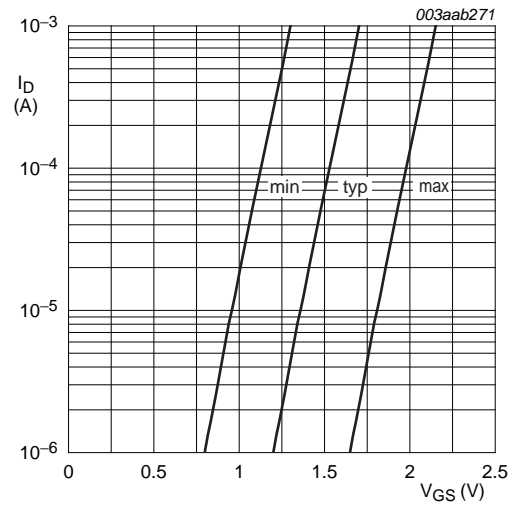
$T_j = 25\text{ }^\circ\text{C}$ and $150\text{ }^\circ\text{C}; V_{DS} > I_D \times R_{DS(on)}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



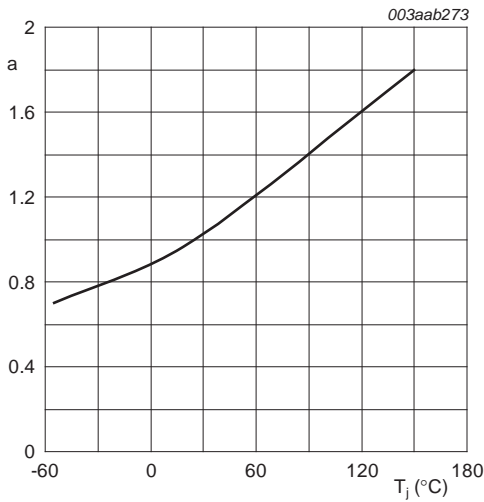
$$I_D = 1\text{ mA}; V_{DS} = V_{GS}$$

Fig 7. Gate-source threshold voltage as a function of junction temperature



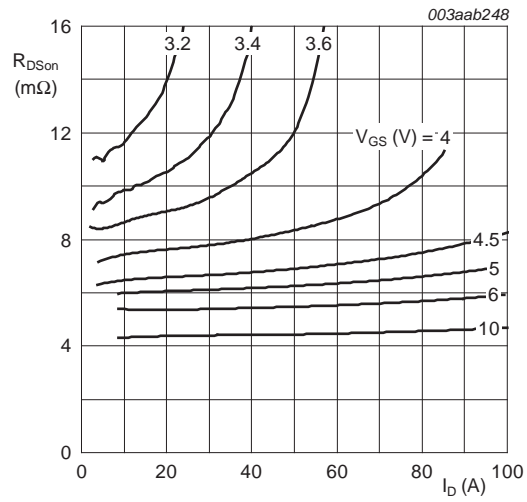
$$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{ V}$$

Fig 8. Sub-threshold drain current as a function of gate-source voltage



$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 9. Normalized drain-source on-state resistance factor as a function of junction temperature



$$T_j = 25\text{ }^\circ\text{C}$$

Fig 10. Drain-source on-state resistance as a function of drain current; typical values

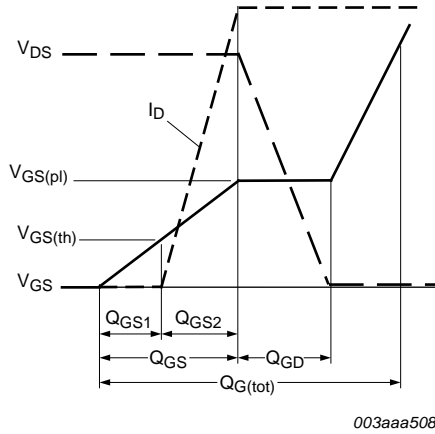


Fig 11. Gate charge waveform definitions

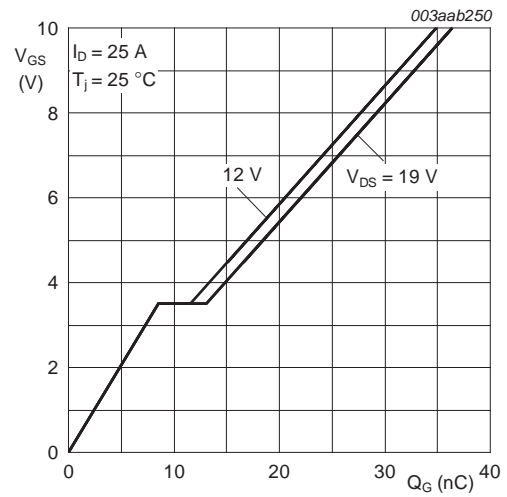


Fig 12. Gate-source voltage as a function of gate charge; typical values

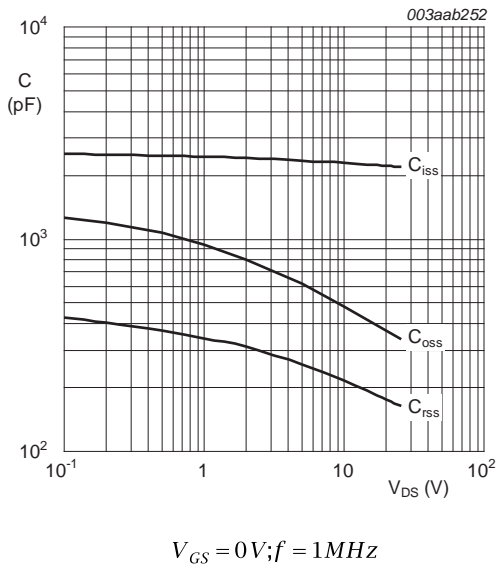


Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

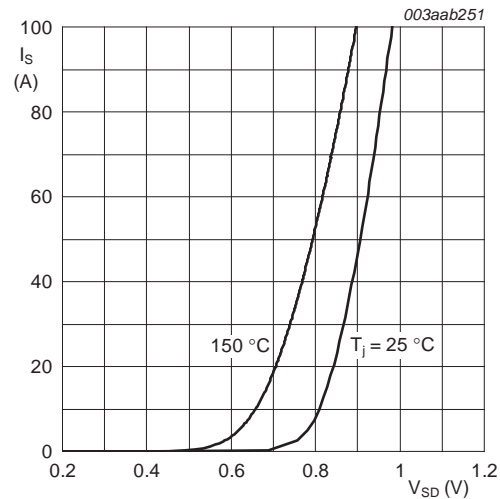


Fig 14. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (LFAK); 4 leads

SOT669

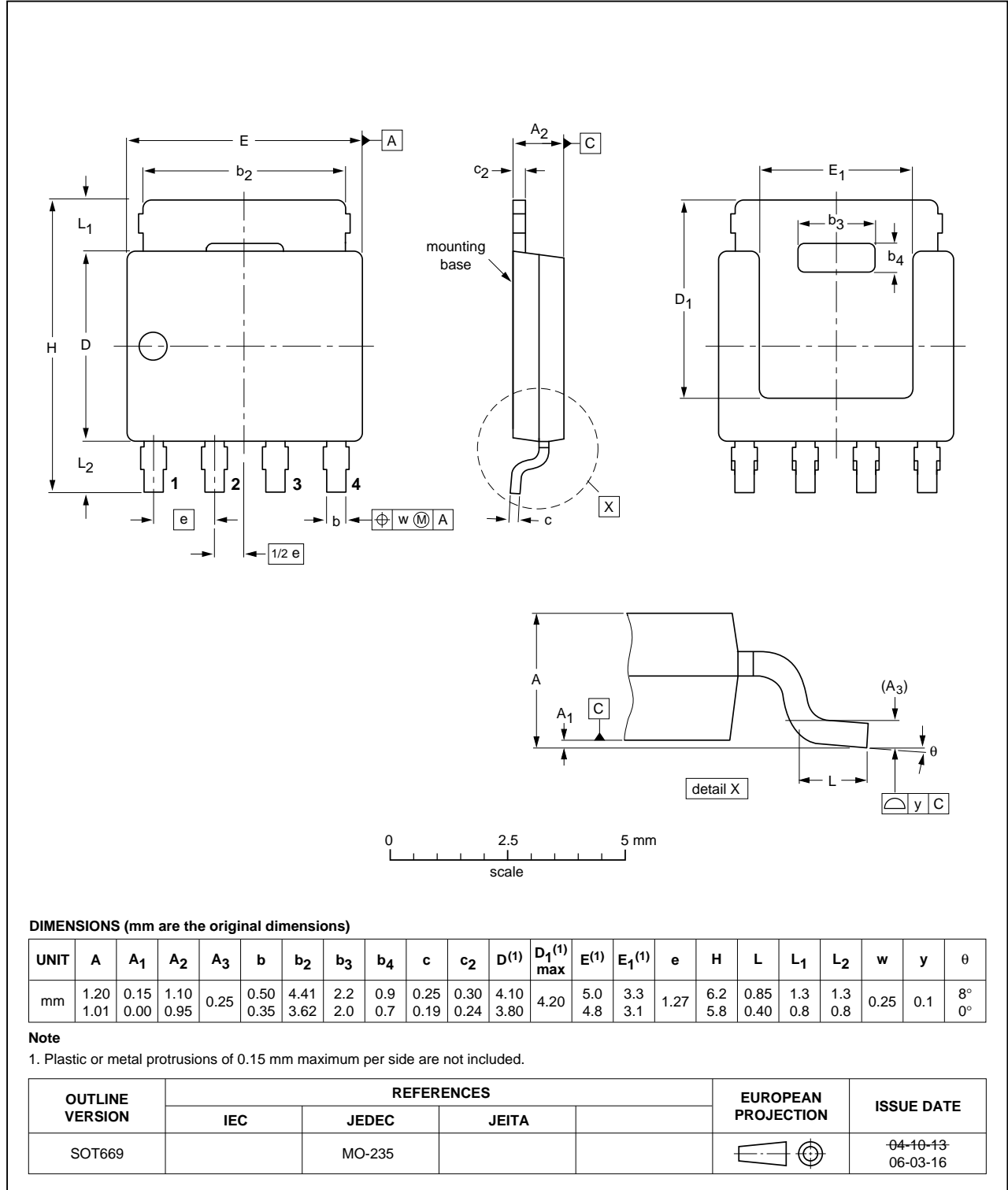


Fig 15. Package outline SOT669 (LFAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PH6030L_1	20080729	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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